



100V 7.4mΩ N-Ch Power MOSFET

Features

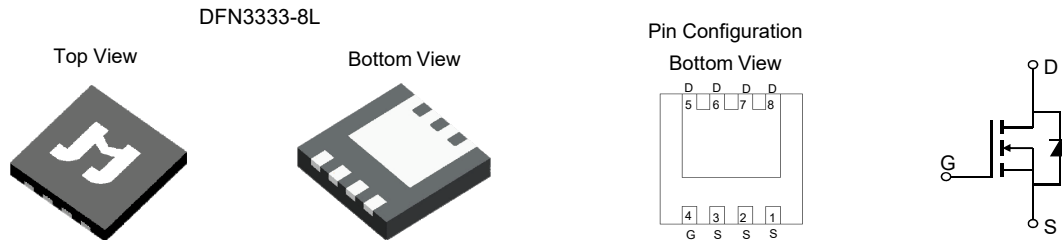
- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th_Typ)}$	1.8	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	36	A
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 10V$)	7.4	mΩ
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 4.5V$)	9.1	mΩ

Applications

- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

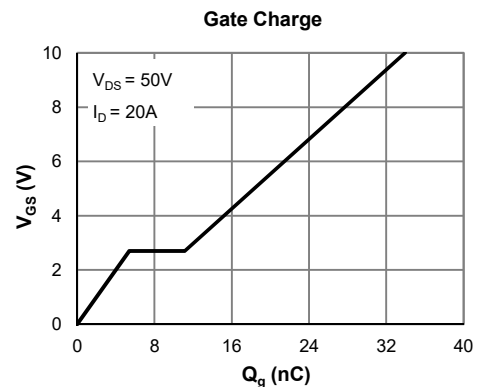
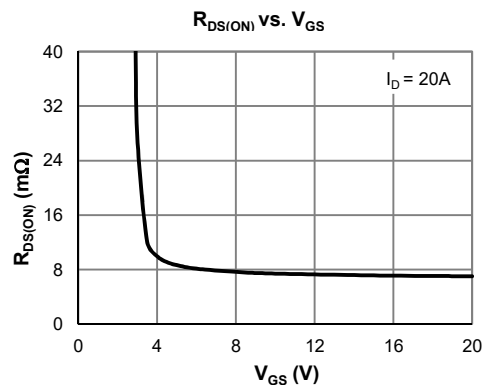


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSL1008AUN-13	DFN3333-8L	8	SL1008A	1	-55 to 150	13-inch Reel	5000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	36
		$T_C = 100^\circ C$	23
Pulsed Drain Current ⁽²⁾	I_{DM}	132	A
Avalanche Current ⁽³⁾	I_{AS}	29	A
Avalanche Energy ⁽³⁾	E_{AS}	122	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	23
		$T_C = 100^\circ C$	9.3
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

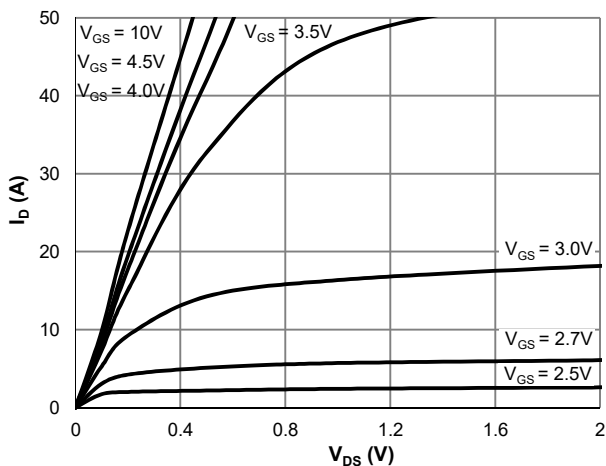
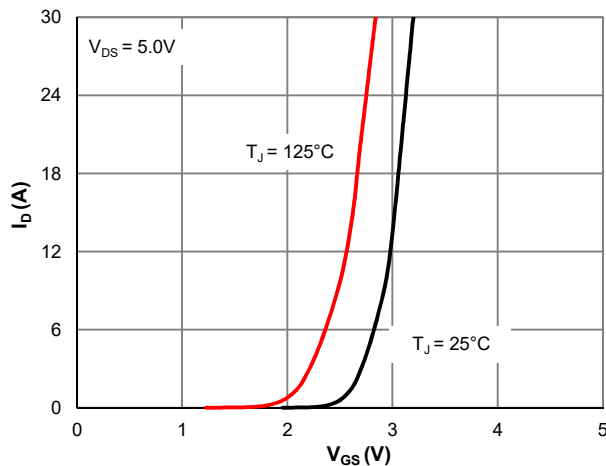
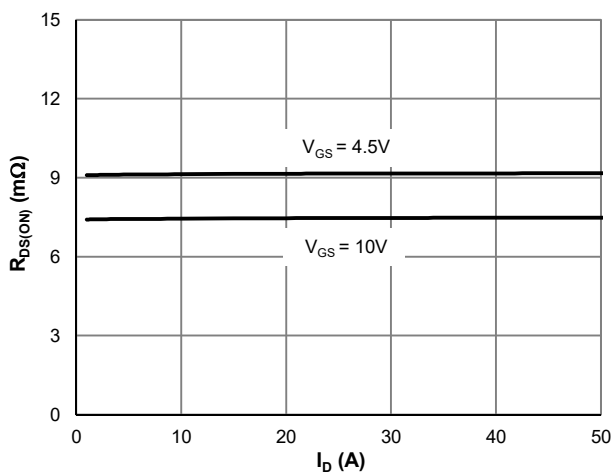
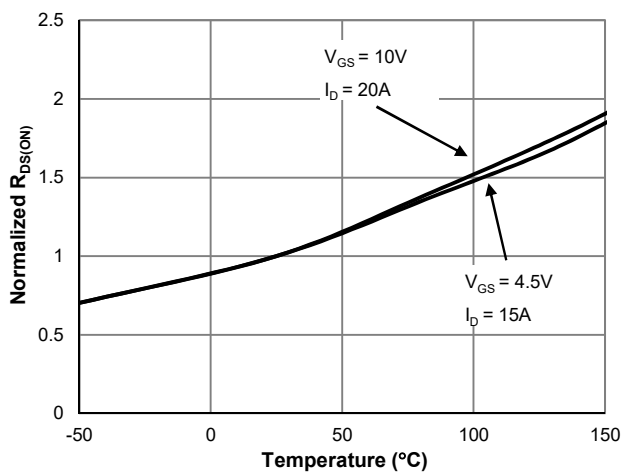
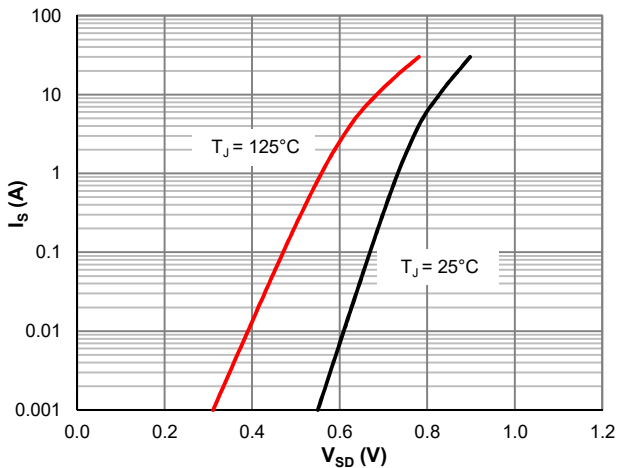
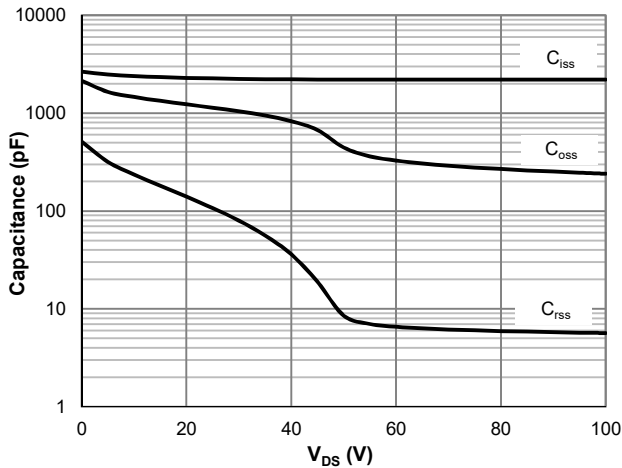
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1.2	1.8	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		7.4	9.3	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}$, $I_D = 15\text{A}$		9.1	11.8	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 20\text{A}$		82		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			23	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$		2200		pF
Output Capacitance	C_{oss}			445		pF
Reverse Transfer Capacitance	C_{rss}			8		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		2.0		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 50\text{V}$, $I_D = 20\text{A}$		34		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			17.0		nC
Gate Source Charge	Q_{gs}			5.5		nC
Gate Drain Charge	Q_{gd}			5.7		nC
Turn-On Delay Time	$t_{D(on)}$			13.0		ns
Turn-On Rise Time	t_r	$V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$		14.0		ns
Turn-Off Delay Time	$t_{D(off)}$	$R_L = 2.5\Omega$, $R_{GEN} = 6\Omega$		29.0		ns
Turn-Off Fall Time	t_f			17.0		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 15\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		49		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		43		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	75	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.5	5.4	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\mu\text{H}$, $V_{GS} = 10\text{V}$, $V_{DS} = 100\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics



Typical Electrical & Thermal Characteristics

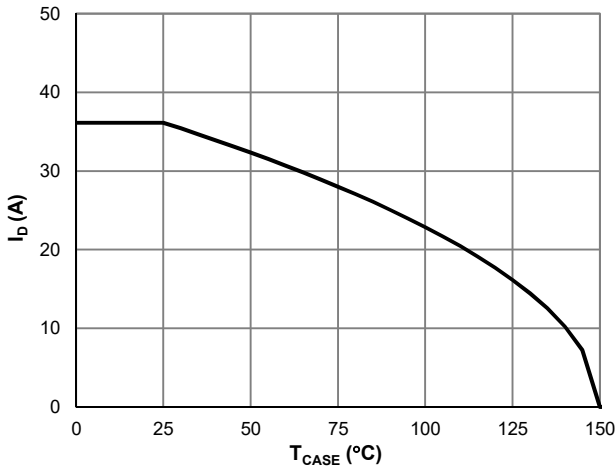


Figure 7: Current De-rating

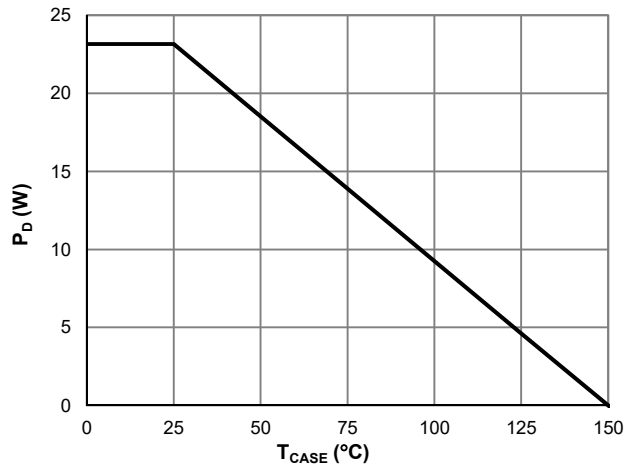


Figure 8: Power De-rating

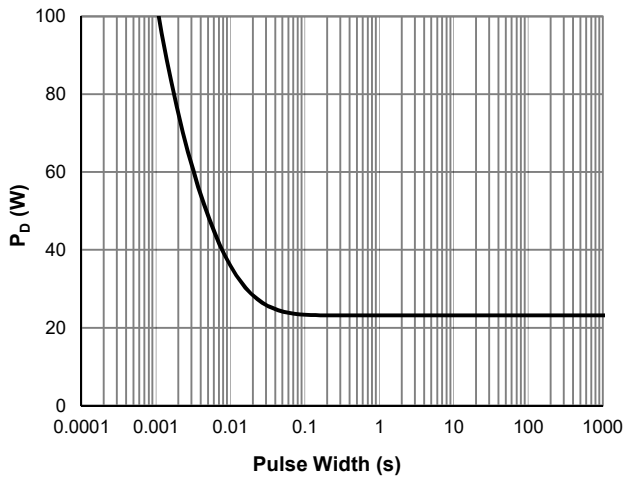
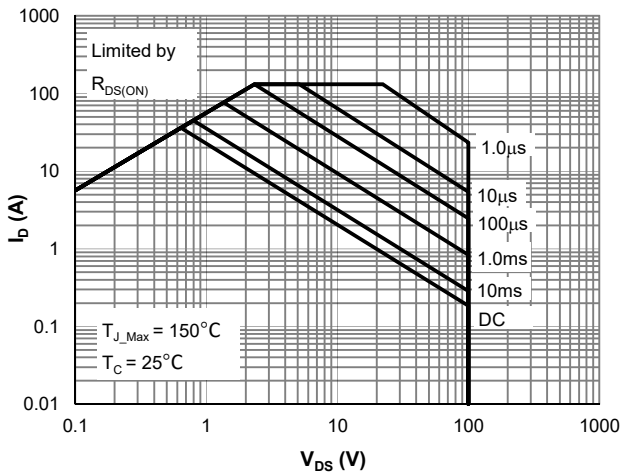


Figure 10: Single Pulse Power Rating, Junction-to-Case

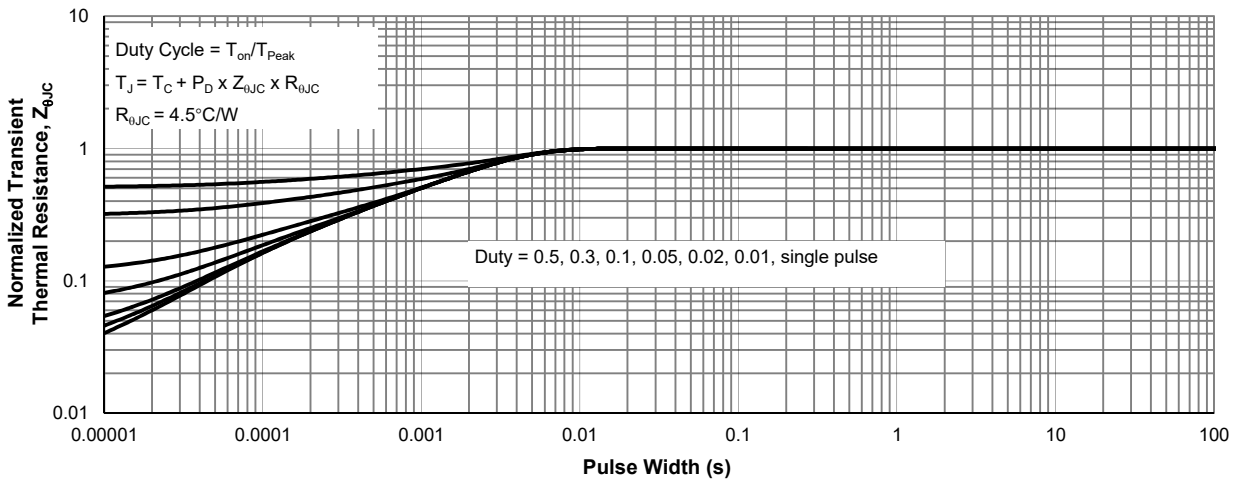
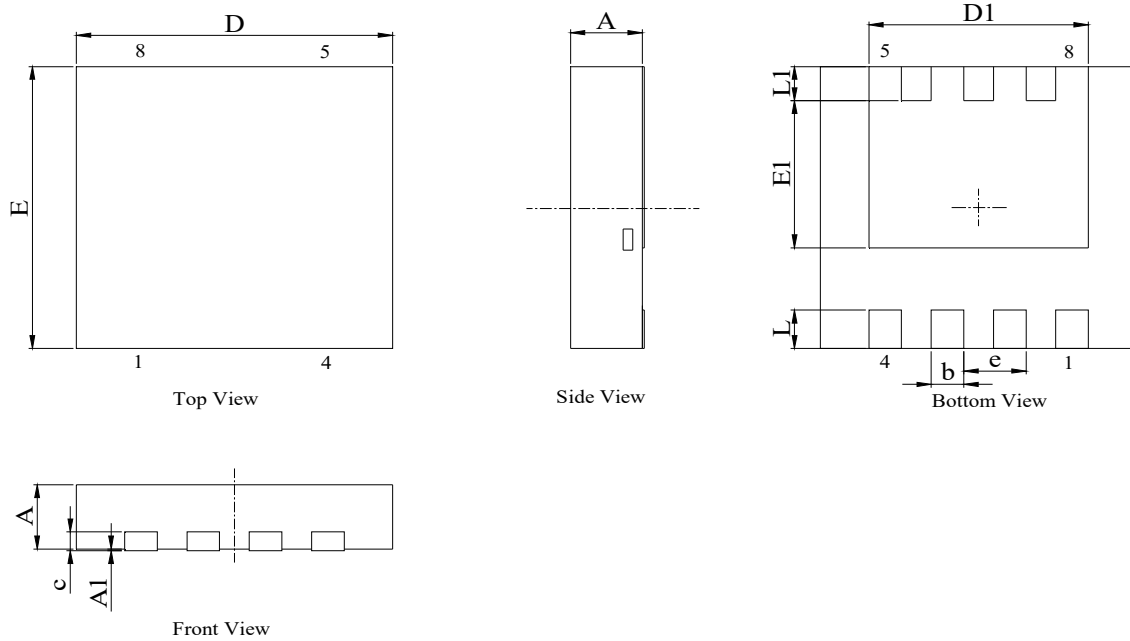


Figure 11: Normalized Maximum Transient Thermal Impedance

DFN3333-8L Package Information
Package Outline


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	--	--	0.05
b	0.29	0.34	0.39
c	--	0.20	--
D	3.20	3.30	3.40
D1	2.19	2.29	2.39
E	3.20	3.30	3.40
E1	1.62	1.72	1.82
L	0.35	0.45	0.55
L1	0.30	0.40	0.50
e	0.65BSC		

Recommended Soldering Footprint
